

## POWER AMPLIFIER APPLICATIONS.

## FEATURES:

- High Voltage :  $V_{CEO} = -120V$
- High Transition Frequency :  $f_T = 120MHz$
- $P_C = 1 \sim 2W$  (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to 2SC2881

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-120	V
Collector-Emitter Voltage	$V_{CEO}$	-120	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-800	mA
Base Current	$I_B$	-160	mA
Collector Power Dissipation	$P_C$	500	mW
Collector Power Dissipation	$P_C^*$	1000	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55 ~ 150	$^\circ C$

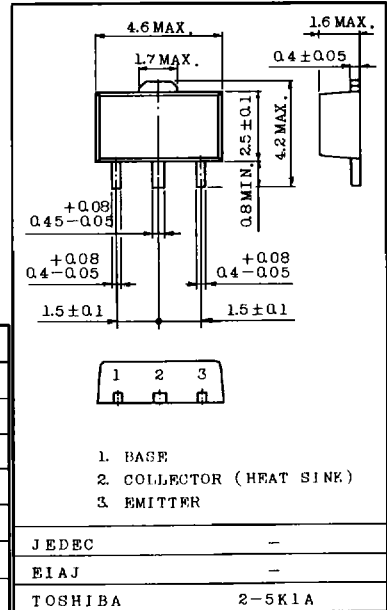
$P_C^*$ : 2SA1201 mounted on ceramic substrate (250mm<sup>2</sup> × 0.8t)

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -120V, I_E = 0$	-	-	-100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-120	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5	-	-	V
DC Current Gain	$h_{FE}$ (Note)	$V_{CE} = -5V, I_C = -100mA$	80	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$	-	-	-1.0	V
Base Emitter Voltage	$V_{BE}$	$V_{CE} = -5V, I_C = -500mA$	-	-	-1.0	V
Transition Frequency	$f_T$	$V_{CE} = -5V, I_C = -100mA$	-	120	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	-	30	pF

Note :  $h_{FE}$  Classification O : 80 ~ 160, Y : 120 ~ 240

Unit in mm



Marking

Type Name

 $h_{FE}$  Rank

